To our customers,

Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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RENESAS

DATA SHEET

SILICON POWER TRANSISTOR
2SB1261-Z

PNP SILICON EPITAXIAL TRANSISTOR

DESCRIPTION

The 2SB1261-Z is designed for Audio Frequency Amplifier and Switching, especially in Hybrid Integrated Circuits.

FEATURES

- High h_{FE} h_{FE} = 100 to 400
- Low $V_{CE(sat)}$ $V_{CE(sat)} \leq 0.3$ V

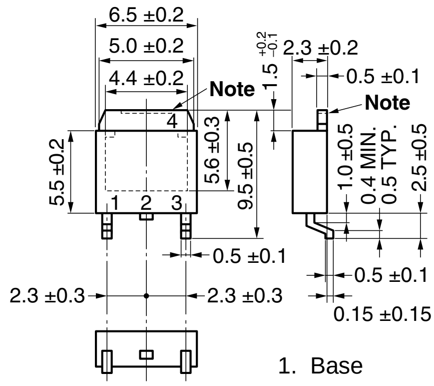
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Collector to Base Voltage	V_{CBO}	–60	V
Collector to Emitter Voltage	V_{CEO}	–60	V
Emitter to Base Voltage	V_{EBO}	–7.0	V
Collector Current (DC)	$I_{C(DC)}$	–3.0	A
Collector Current (pulse) Note 1	$I_{C(pulse)}$	–5.0	A
Base Current (DC)	$I_{B(DC)}$	–0.5	A
Total Power Dissipation (T_A = 25°C) Note 2	P_{T1}	2.0	W
Total Power Dissipation (T_C = 25°C)	P_{T2}	10	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C

Notes 1. PW ≤ 10 ms, Duty Cycle ≤ 50%

2. When mounted on ceramic substrate of 7.5 cm^2 × 0.7 mm

PACKAGE DRAWING (Unit: mm)



TO-252 (MP-3Z)

1. Base
2. Collector
3. Emitter
4. Collector Fin

Note The depth of notch at the top of the fin is from 0 to 0.2 mm.

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Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.

Document No. D18262EJ4V0DS00 (4th edition)
Date Published December 2007 NS
Printed in Japan

The mark <R> shows major revised points.
The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			–10	μA	V_{CB} = –60 V, I_E = 0
Emitter Cutoff Current	I_{EBO}			–10	μA	V_{EB} = –7.0 V, I_C = 0
DC Current Gain	h_{FE1}*	60				V_{CE} = –2.0 V, I_C = –0.2 A
DC Current Gain	h_{FE2}*	100		400		V_{CE} = –2.0 V, I_C = –0.6 A
DC Current Gain	h_{FE3}*	50				V_{CE} = –2.0 V, I_C = –2.0 A
Collector Saturation Voltage	$V_{CE(sat)}$*		–0.2	–0.3	V	I_C = –1.5 A, I_B = –0.15 A
Base Saturation Voltage	$V_{BE(sat)}$*		–0.94	–1.2	V	I_C = –1.5 A, I_B = –0.15 A
Gain Bandwidth Product	f_T		50		MHz	V_{CE} = –5.0 V, I_E = 1.5 A
Output Capacitance	C_{ob}		40		pF	V_{CB} = –10 V, I_E = 0, f ≒ 1.0 MHz
Turn-on Time	t_{on}		0.15	0.5	μs	I_C = –1.0 A, V_{CC} ≒ –10 V, R_L = 10 Ω, I_{B1} = –I_{B2}= –0.1 A
Storage Time	t_{stg}		0.5	2.0	μs	
Fall time	t_f		0.1	0.5	μs	

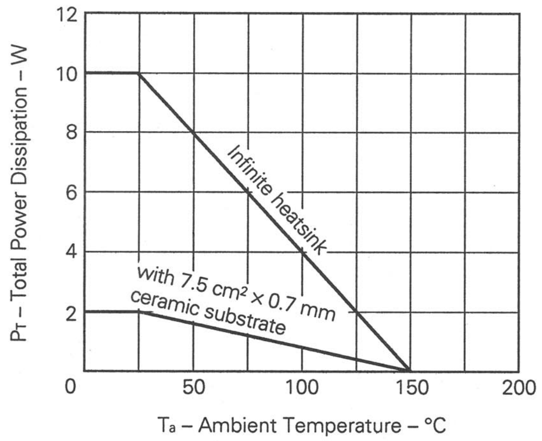
* Pulsed: PW ≦ 350 μs, Duty Cycle ≦ 2 %

h_{FE} Classification

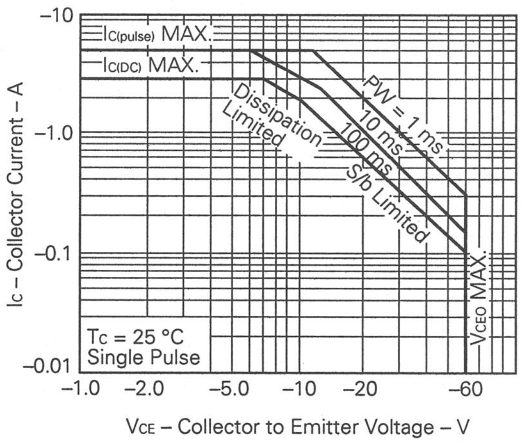
MARKING	M	L	K
h_{FE2}	100 to 200	160 to 320	200 to 400

TYPICAL CHARACTERISTICS (T_a = 25 °C)

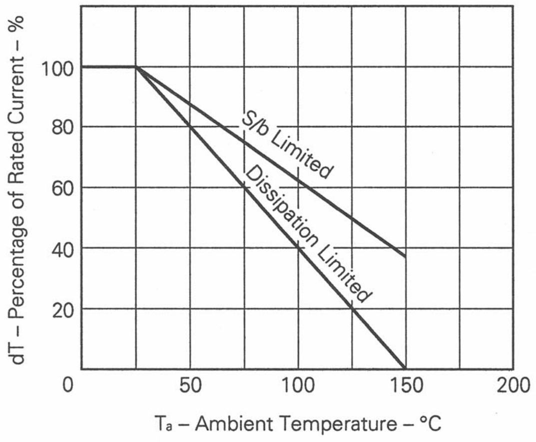
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



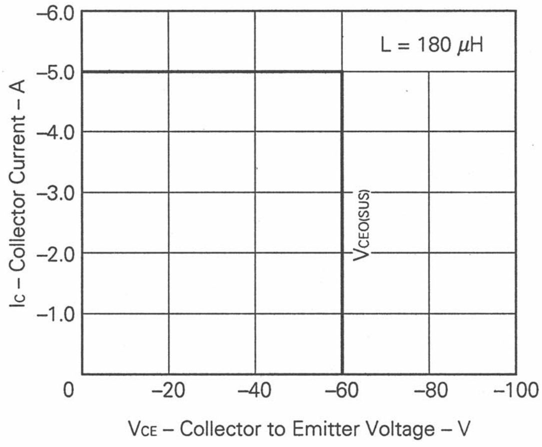
FORWARD BIAS SAFE OPERATING AREA



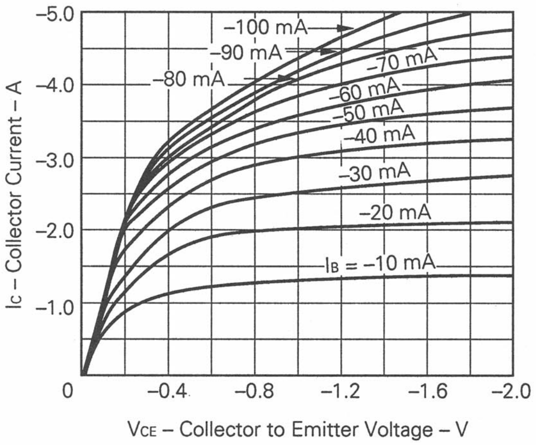
DERATING CURVE OF SAFE OPERATING AREA



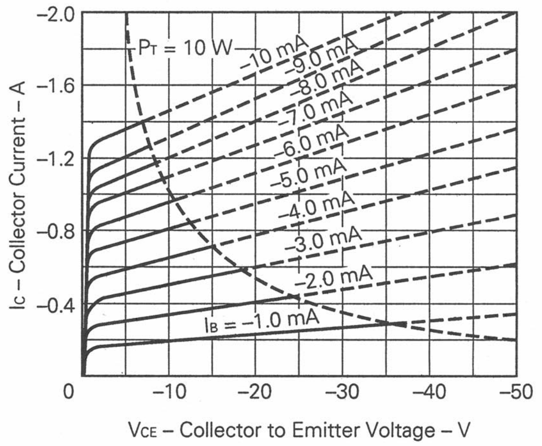
RESERVE BIAS SAFE OPERAING AREA



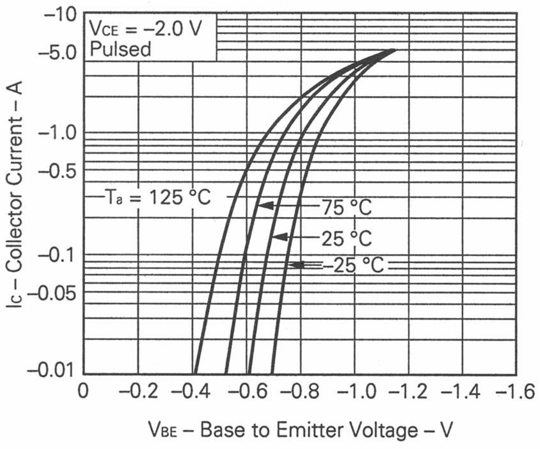
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



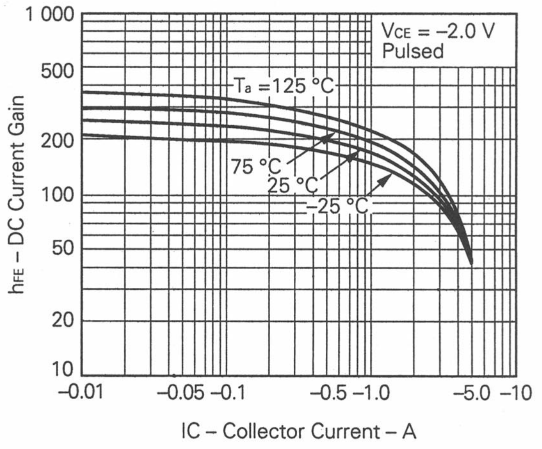
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



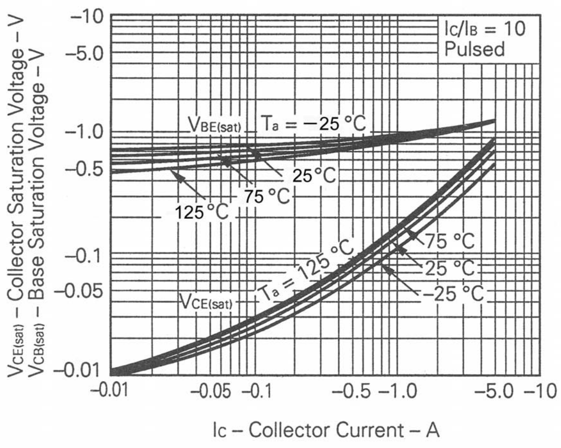
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



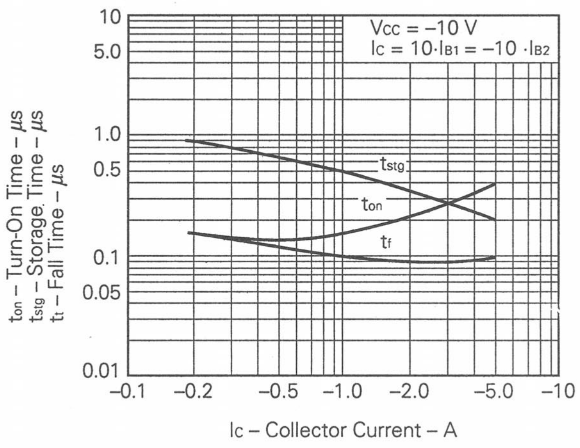
DC CURRENT GAIN vs. COLLECTOR CURRENT



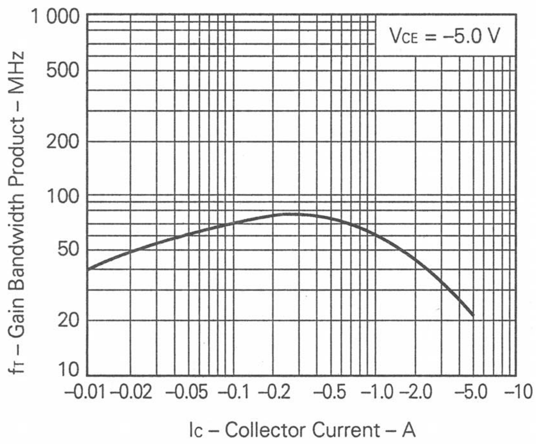
<R> **BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT**



FALL, STORAGE AND TURN-ON TIME vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE